

VERTICAL DEFLECTION BOOSTER

ADVANCE DATA

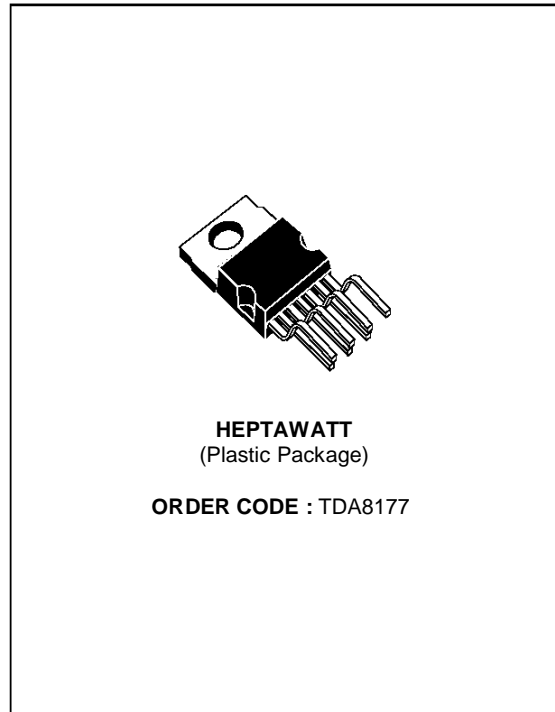
- POWER AMPLIFIER
- FLYBACK GENERATOR
- THERMAL PROTECTION
- OUTPUT CURRENT UP TO 3.0A_{PP}
- FLYBACK VOLTAGE UP TO 70V (on Pin 5)
- SUITABLE FOR DC COUPLING APPLICATION

DESCRIPTION

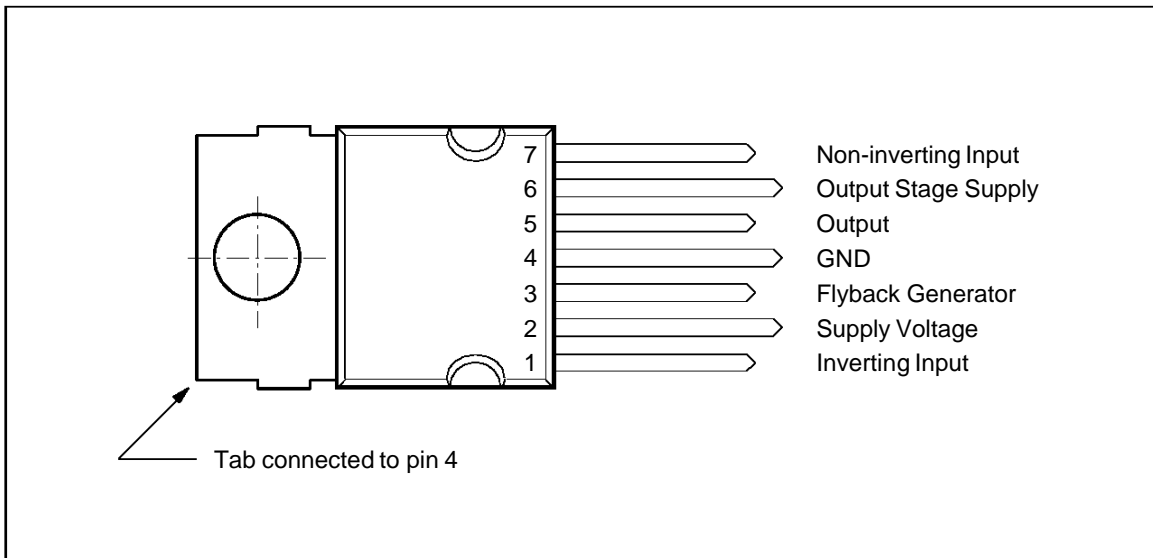
Designed for monitors and high performance TVs, the TDA8177 vertical deflection booster delivers flyback voltages up to 70V.

The TDA8177 operates with supplies up to 35V and provides up to 3A_{pp} output current to drive the yoke.

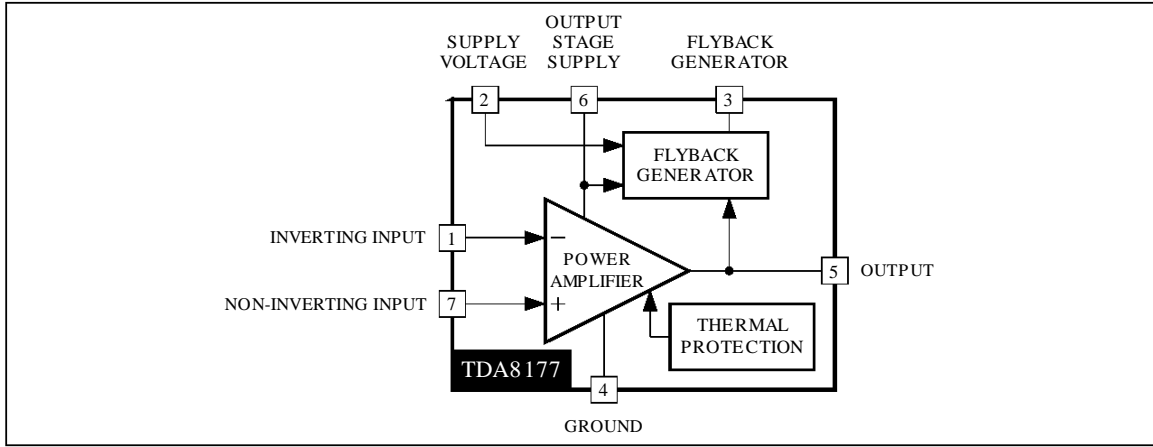
The TDA8177 is offered in HEPTAWATT package.



PIN CONNECTIONS



BLOCK DIAGRAM



8177-02.EPS

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_S	Supply Voltage (Pin 2) (see note 1)	40	V
V_6	Flyback Peak Voltage (Pin 6) (see note 1)	75	V
V_1, V_7	Amplifier Input Voltage (Pins 1-7) (see note 1)	- 0.3, + V_S	V
I_O	Maximum Output Peak Current (see notes 2 and 3)	2.5	A
I_3	Maximum Sink Current (first part of flyback) ($t < 1\text{ms}$)	2.5	A
I_3	Maximum Source Current ($t < 1\text{ms}$)	2.5	A
V_{ESD}	Electrostatic Handling for all pins (see note 4)	2000	V
T_{oper}	Operating Ambient Temperature	- 20, + 75	°C
T_{stg}	Storage Temperature	- 40, + 150	°C
T_j	Junction Temperature	+150	°C

8177-01.TBL

- Notes :**
1. Versus GND.
 2. The output current can reach 4A peak for $t \leq 10\mu\text{s}$ (up to 120Hz).
 3. Provided SOAR is respected (see Figures 1 and 2).
 4. Equivalent to discharging a 100pF capacitor through a 1.5k Ω series resistor.

THERMAL DATA

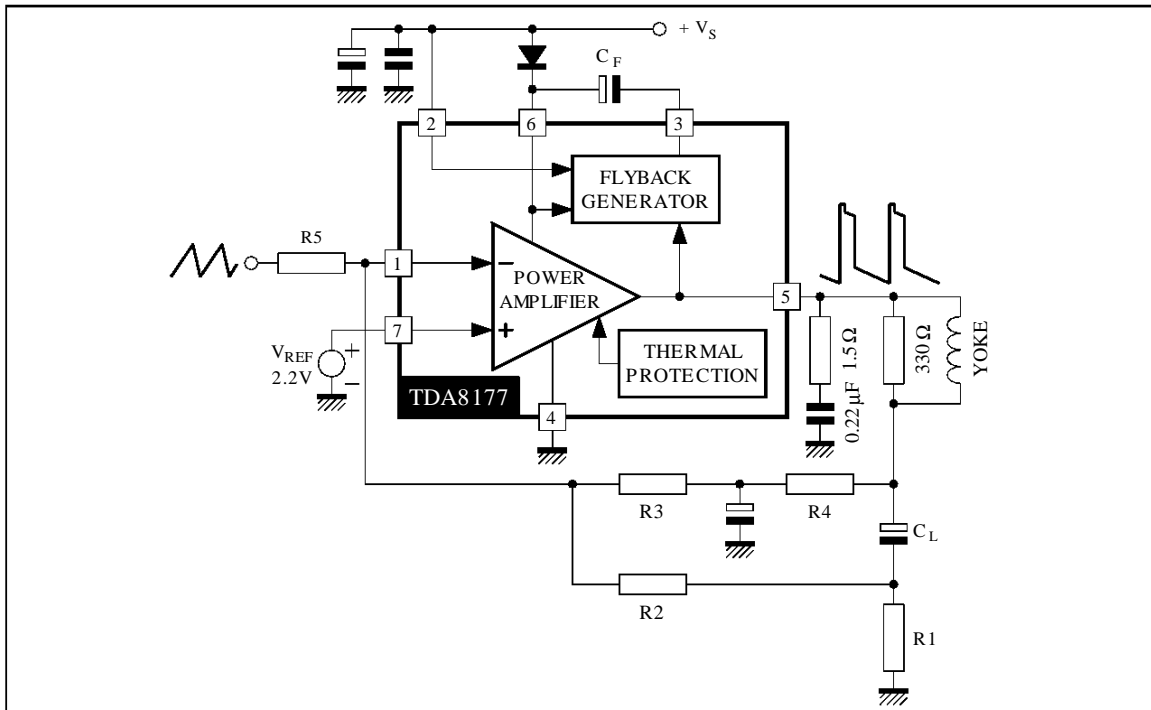
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	Junction-case Thermal Resistance Max.	3	°C/W
T_t	Temperature for Thermal Shutdown	150	°C
T_{jr}	Recommended Max. Junction Temperature	120	°C

8177-02.TBL

ELECTRICAL CHARACTERISTICS(V_S = 35V, T_A = 25°C, unless otherwise specified)

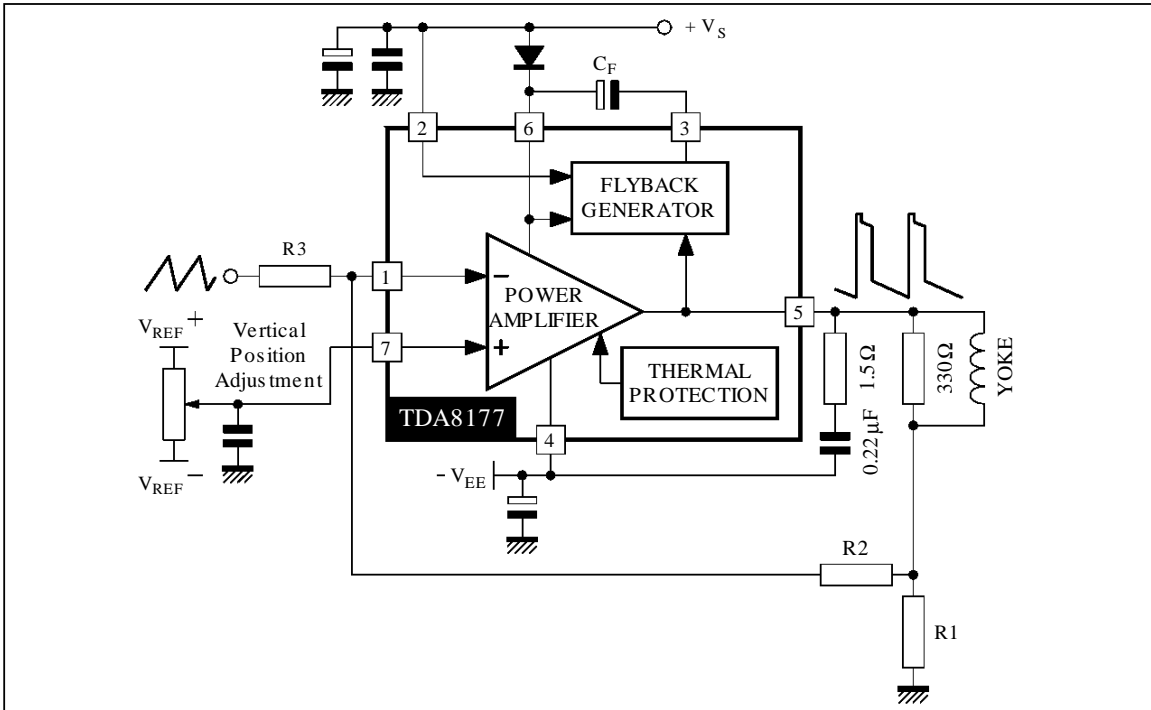
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit	
V _S	Operating Supply Voltage Range		10		35	V	
I ₂	Pin 2 Quiescent Current	I ₃ = 0, I ₅ = 0		9	20	mA	
I ₆	Pin 6 Quiescent Current	I ₃ = 0, I ₅ = 0, V ₆ = 35V		8	15	30	mA
I _O	Max. Peak Output Current				1.5	A	
I ₁	Amplifier Bias Current	V ₁ = 22V, V ₇ = 23V		- 0.15	- 1	μA	
I ₇	Amplifier Bias Current	V ₁ = 23V, V ₇ = 22V		- 0.15	- 1	μA	
V _{IO}	Offset Voltage				7	mV	
ΔV _{IO} /dt	Offset Drift versus Temperature			- 10		μV/°C	
GV	Voltage Gain		80			dB	
V _{5L}	Output Saturation Voltage to GND (Pin 4)	I ₅ = 1.5A		1	1.7	V	
V _{5H}	Output Saturation Voltage to Supply (Pin 6)	I ₅ = - 1.5A		1.8	2.3	V	
V _{D5-6}	Diode Forward Voltage between Pins 5-6	I ₅ = 1.5A		1.8	2.3	V	
V _{D3-2}	Diode Forward Voltage between Pins 3-2	I ₃ = 1.5A		1.6	2.2	V	
V _{3SL}	Saturation Voltage on Pin 3	I ₃ = 20mA		0.4	1	V	
V _{3SH}	Saturation Voltage to Pin 2 (2nd part of flyback)	I ₃ = - 1.5A		2.1	2.8	V	

8177-03.TBL

APPLICATION CIRCUITS**AC COUPLING**

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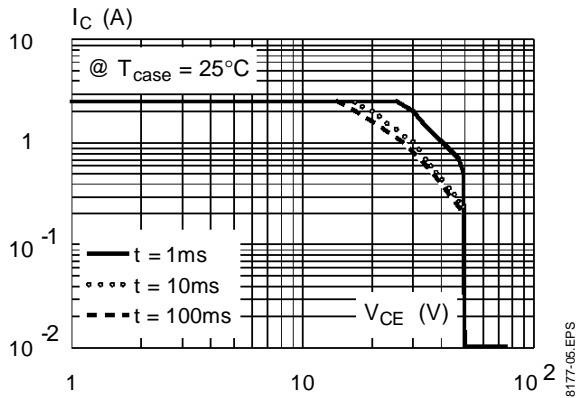
APPLICATION CIRCUITS (continued)
DC COUPLING



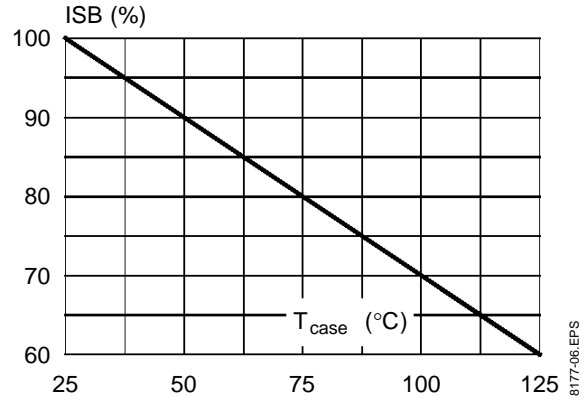
8177-04.EPS

Figure 1 : Output Transistors SOA
(for secondary breakdown)

Figure 2 : Secondary Breakdown Temperature
Derating Curve
(ISB = secondary breakdown current)

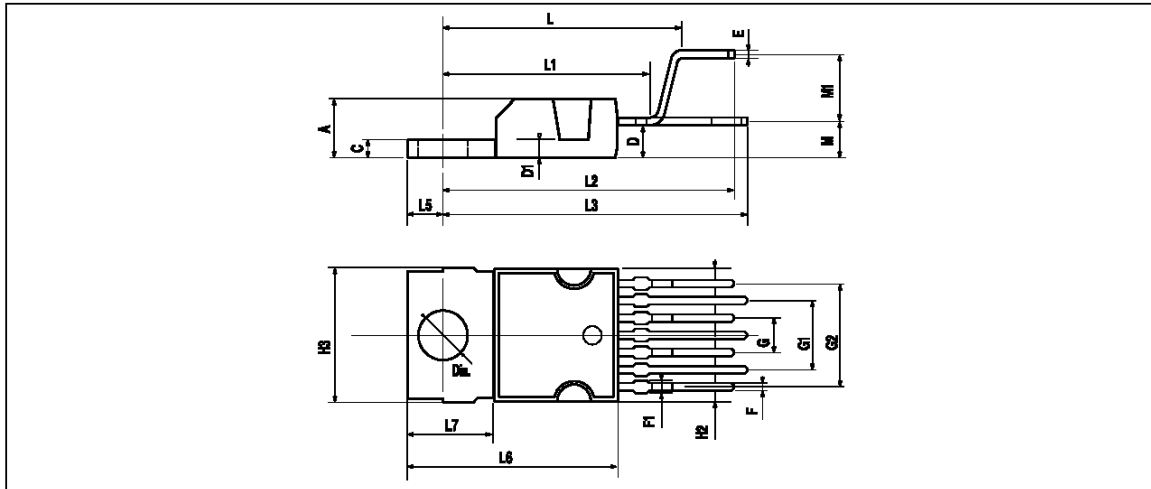


8177-06.EPS



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PACKAGE MECHANICAL DATA : HEPTAWATT



PM-HEPTV.EPS

Dimensions	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			4.8			0.189
C			1.37			0.054
D	2.4		2.8	0.094		0.110
D1	1.2		1.35	0.047		0.053
E	0.35		0.55	0.014		0.022
F	0.6		0.8	0.024		0.031
F1			0.9			0.035
G	2.41	2.54	2.67	0.095	0.100	0.105
G1	4.91	5.08	5.21	0.193	0.200	0.205
G2	7.49	7.62	7.8	0.295	0.300	0.307
H2			10.4			0.409
H3	10.05		10.4	0.396		0.409
L		16.97			0.668	
L1		14.92			0.587	
L2		21.54			0.848	
L3		22.62			0.891	
L5	2.6		3	0.102		0.118
L6	15.1		15.8	0.594		0.622
L7	6		6.6	0.236		0.260
M		2.8			0.110	
M1		5.08			0.200	
Dia.	3.65		3.85	0.144		0.152

HEPTV.TBL

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